



# ACE1A1516B

## N-Channel Enhancement Mode Field Effect Transistor

### Description

The ACE1A1516B uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as Battery protection or in other switching application.

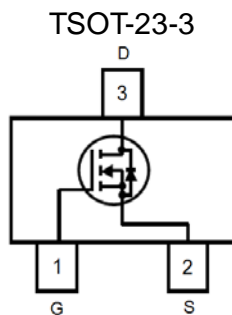
### Features

- $V_{DS} (V) = 60V, I_D = 3A$
- $R_{DS(ON)} < 105m\Omega @ V_{GS} = 10V$
- $R_{DS(ON)} < 125m\Omega @ V_{GS} = 4.5V$
- TSOT-23-3 Package

### Absolute Maximum Ratings

| Parameter                                   | Symbol          | Max                | Unit       |
|---|-----------------|--------------------|------------|
| Drain-Source Voltage                        | $V_{DSS}$       | 60                 | V          |
| Gate-Source Voltage                         | $V_{GSS}$       | $\pm 20$           | V          |
| Drain Current (Continuous)                  | $I_D$           | $T_A = 25^\circ C$ | 3          |
|   |                 | $T_A = 70^\circ C$ | 2.4        |
| Drain Current (Pulsed)                      | $I_{DM}$        | 10                 | A          |
| Power Dissipation                           | $P_D$           | $T_A = 25^\circ C$ | 1.7        |
|   |                 | $T_A = 70^\circ C$ | 0.85       |
| Operating temperature / storage temperature | $T_J / T_{STG}$ | -55~150            | $^\circ C$ |

### Packaging Type



### Ordering information

ACE1A1516B XX + H

- └─ Halogen - free
- └─ Pb - free
- └─ BMS: TSOT-23-3



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### Electrical Characteristics

$T_A=25^{\circ}\text{C}$ , unless otherwise specified.

| Parameter                             | Symbol        | Test Conditions                                     | Min | Typ  | Max       | Unit       |
|---------------------------------------|---------------|---|-----|------|-----------|------------|
| Static                                |               |   |     |      |           |            |
| Drain-source breakdown voltage        | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=250\mu A$                           | 60  |      |           | V          |
| Zero gate voltage drain current       | $I_{DSS}$     | $V_{DS}=60V, V_{GS}=0V$                             |     |      | 1         | $\mu A$    |
| Gate threshold voltage                | $V_{GS(th)}$  | $V_{GS}=V_{DS}, I_{DS}=250\mu A$                    | 1.3 | 1.7  | 2.5       | V          |
| Gate leakage current                  | $I_{GSS}$     | $V_{GS}=\pm 20V, V_{DS}=0V$                         |     |      | $\pm 100$ | nA         |
| Drain-source on-state resistance      | $R_{DS(on)}$  | $V_{GS}=10V, I_D=3A$                                |     | 82   | 105       | m $\Omega$ |
|                                       |               | $V_{GS}=4.5V, I_D=3A$                               |     | 102  | 125       |            |
| Forward trans conductance             | $g_{FS}$      | $V_{DS}=15V, I_D=2A$                                |     | 3    |           | S          |
| Diode forward voltage                 | $V_{SD}$      | $I_{SD}=1A, V_{GS}=0V$                              |     |      | 1.0       | V          |
| Maximum Body-Diode Continuous Current | $I_S$         |   |     |      | 3         | A          |
| Switching                             |               |   |     |      |           |            |
| Total gate charge                     | $Q_g$         | $V_{GS}=4.5V, V_{DS}=30V, I_D=3A$                   |     | 6    |           | nC         |
| Gate-source charge                    | $Q_{gs}$      |   |     | 1    |           |            |
| Gate-drain charge                     | $Q_{gd}$      |   |     | 1.3  |           |            |
| Turn-on delay time                    | $t_{d(on)}$   | $V_{GS}=10V, I_D=1.5A, V_{DS}=30V, R_{GEN}=1\Omega$ |     | 6    |           | ns         |
| Turn-on rise time                     | $T_r$         |   |     | 15   |           |            |
| Turn-off delay time                   | $t_{d(off)}$  |   |     | 15   |           |            |
| Turn-off fall time                    | $T_f$         |   |     | 10   |           |            |
| Dynamic                               |               |   |     |      |           |            |
| Input capacitance                     | $C_{iss}$     | $V_{GS}=0V, V_{DS}=30V, f=1.0MHz$                   |     | 247  |           | pF         |
| Output capacitance                    | $C_{oss}$     |   |     | 34   |           |            |
| Reverse transfer capacitance          | $C_{rss}$     |   |     | 19.5 |           |            |

#### Notes:

1. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The value in any given application depends on the user's specific board design.
2. Repetitive rating, pulse width limited by junction temperature.
3. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JA}$  and lead to ambient.
4. The static characteristics in Figures 1 to 6 are obtained using <300  $\mu s$  pulses, duty cycle 0.5% max.
5. These tests are performed with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The SOA curve provides a single pulse rating.
6. The current rating is based on the  $t \leq 10s$  thermal resistance rating.



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### Typical Performance Characteristics

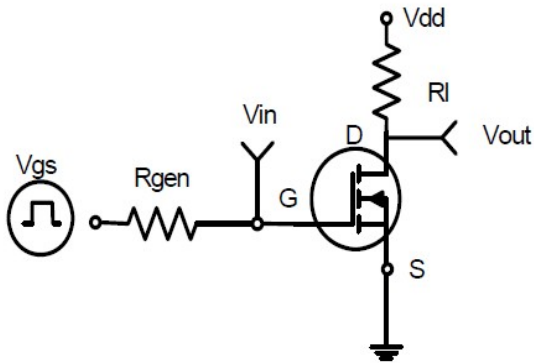


Figure 1: Switching Test Circuit

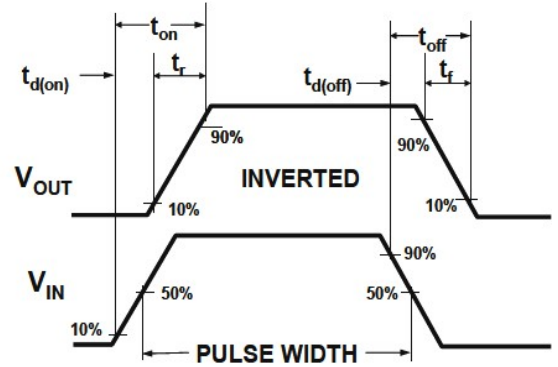


Figure 2: Switching Waveforms

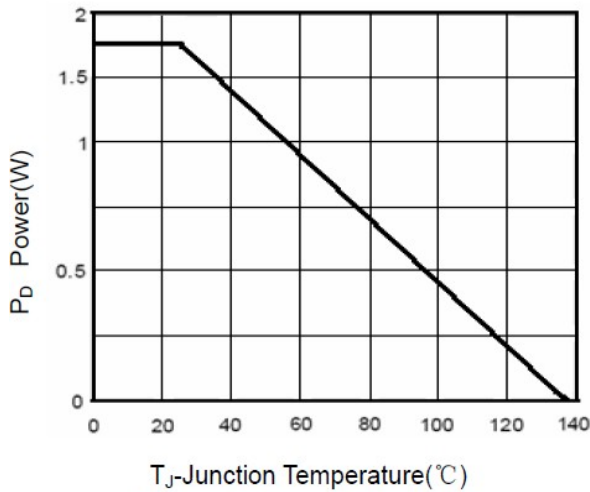


Figure 3 Power Dissipation

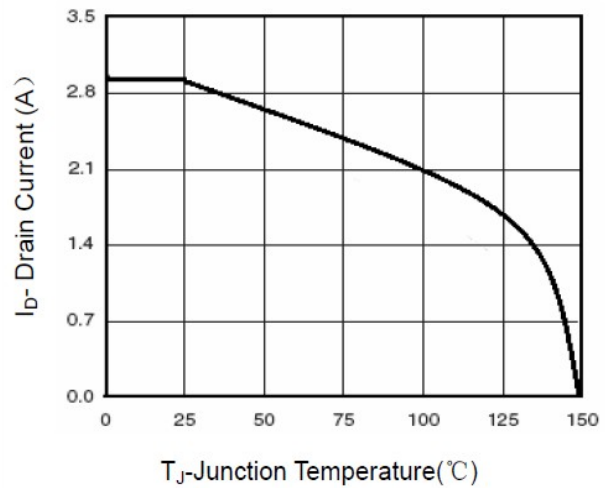


Figure 4 Drain Current

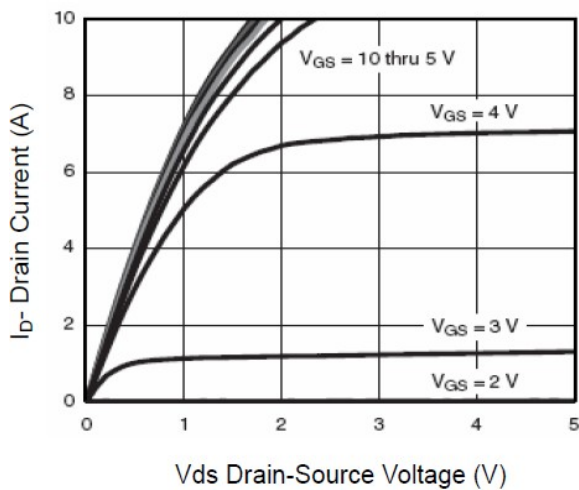


Figure 5 Output Characteristics

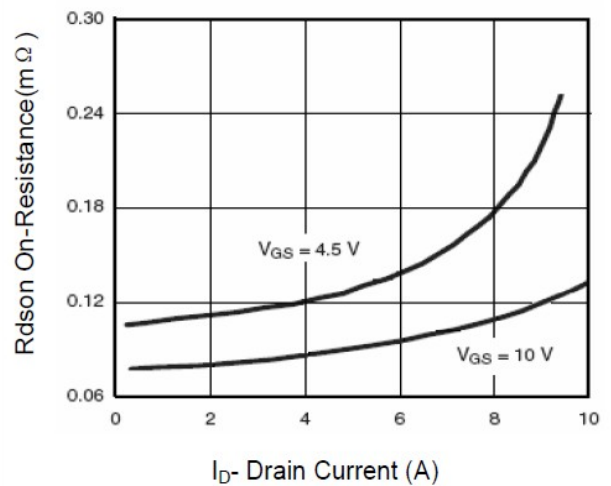
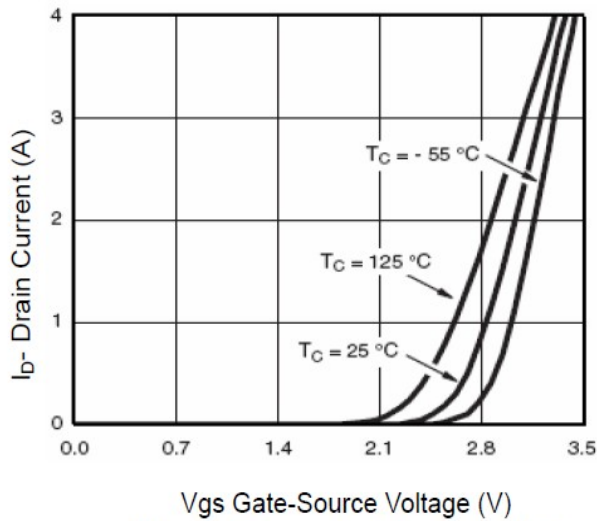


Figure 6 Drain-Source On-Resistance

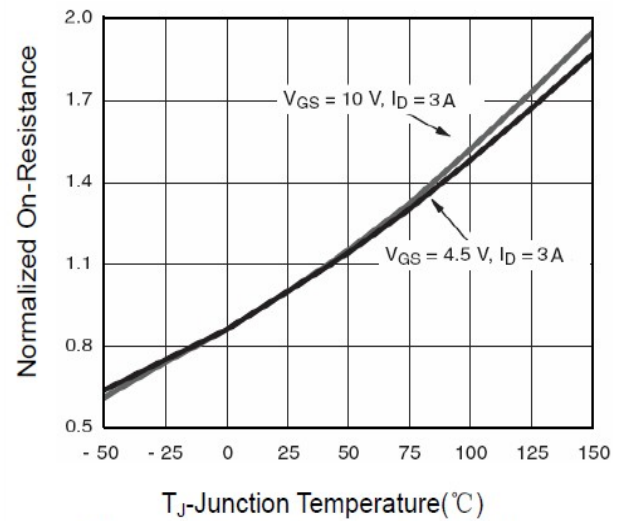


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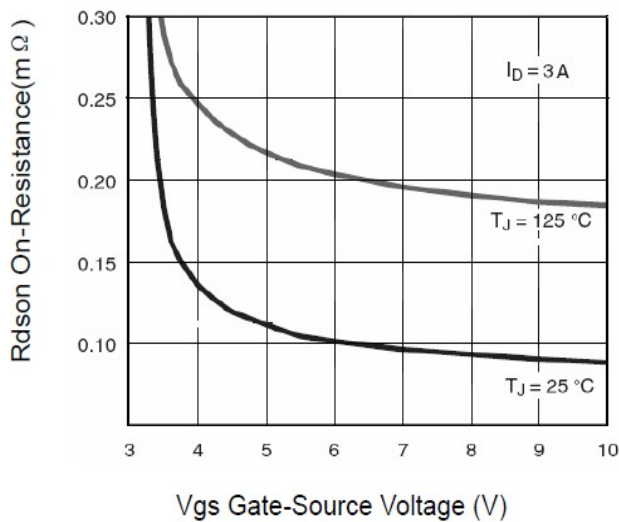
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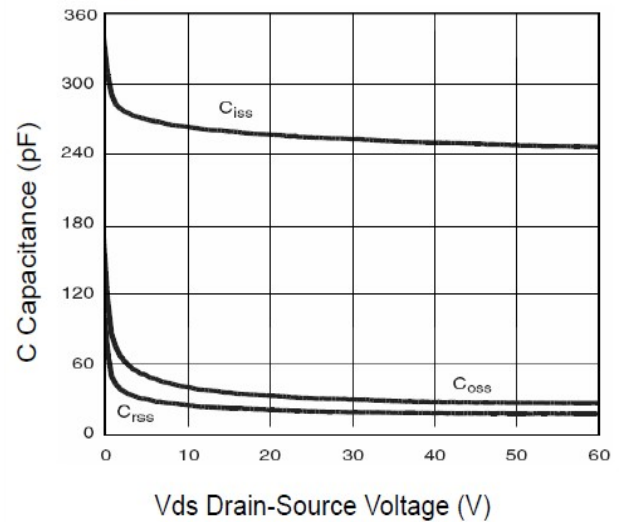
**Figure 7 Transfer Characteristics**



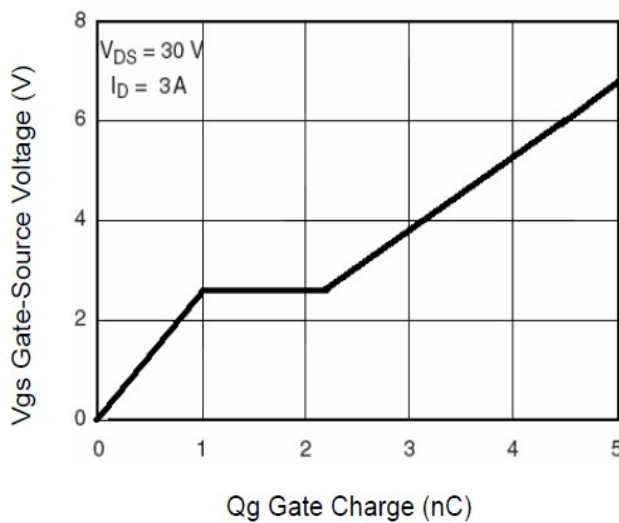
**Figure 8 Drain-Source On-Resistance**



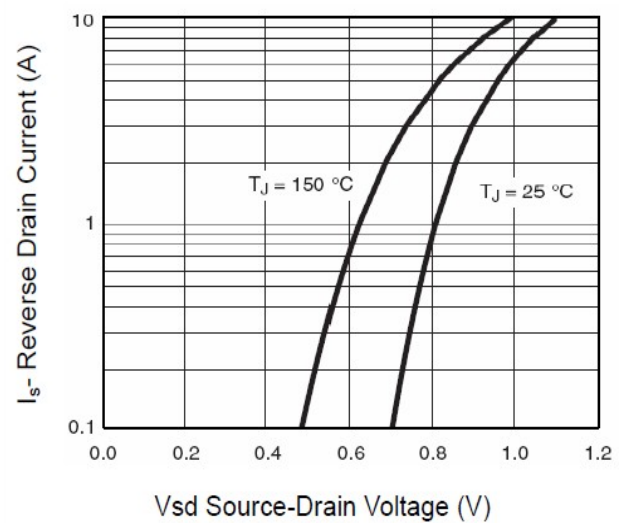
**Figure 9 Rdson vs Vgs**



**Figure 10 Capacitance vs Vds**



**Figure 11 Gate Charge**

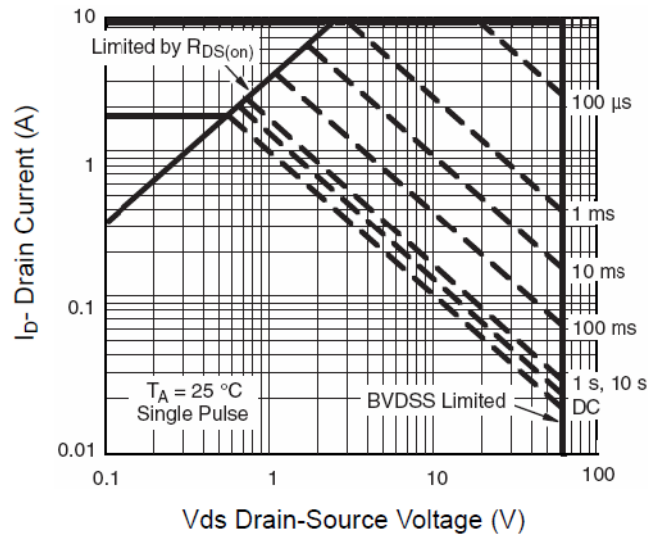


**Figure 12 Source- Drain Diode Forward**

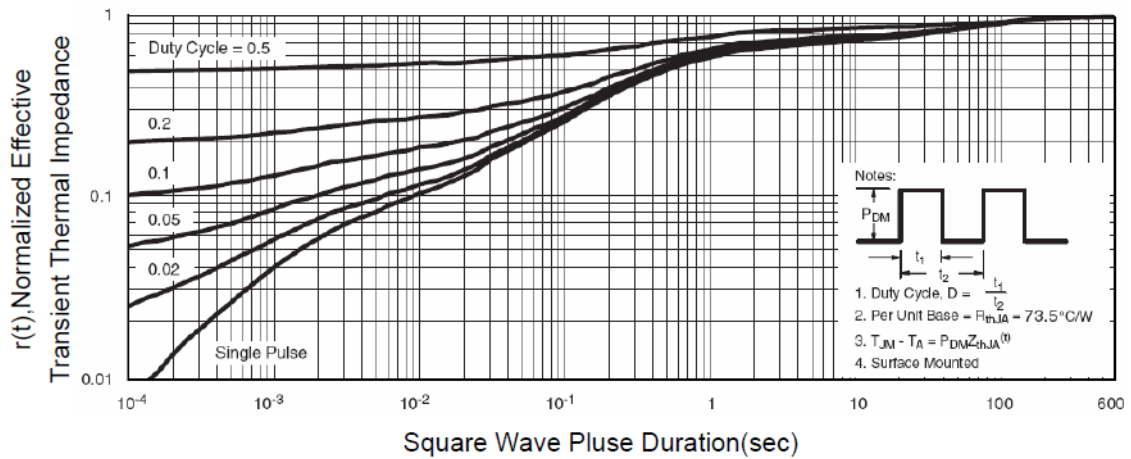


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**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

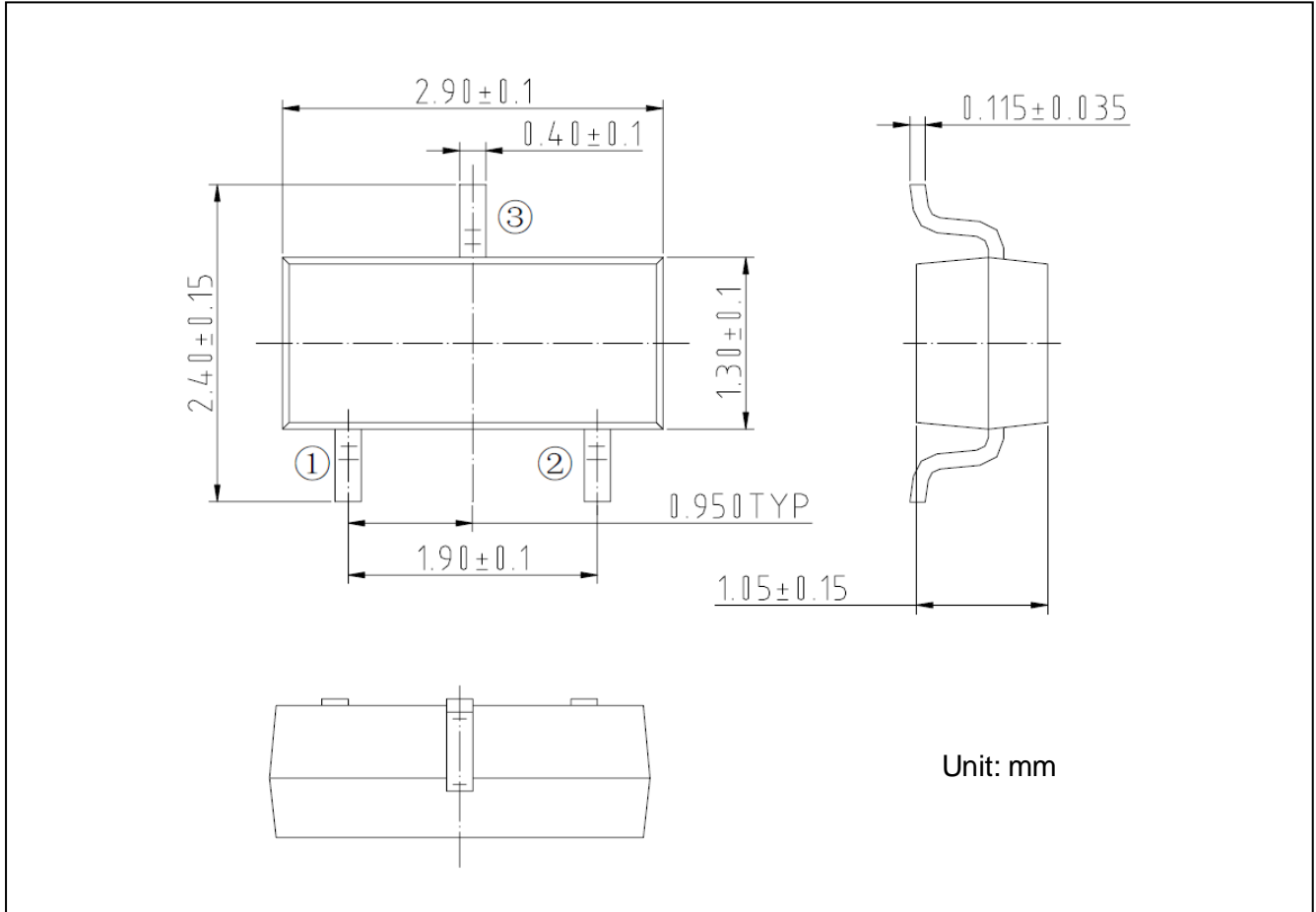


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### Packing Information

#### TSOT-23-3





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### Notes

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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